

CBAS17

**SURFACE MOUNT
LOW VOLTAGE
SILICON STABISTOR**



SOT-23 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBAS17 type is a planar epitaxial silicon switching diode, designed for low voltage stabilizing applications.

MARKING CODE: A91

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

Peak Repetitive Forward Current

Power Dissipation

Operating and Storage Junction Temperature

Thermal Resistance

SYMBOL

I_{FRM}

P_D

T_J, T_{stg}

Θ_{JA}

250

350

-65 to +150

357

UNITS

mA

mW

$^{\circ}\text{C}$

$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=4.0\text{V}$			5.0	μA
V_F	$I_F=0.1\text{mA}$	580	665	680	mV
V_F	$I_F=1.0\text{mA}$	665	745	760	mV
V_F	$I_F=5.0\text{mA}$	725	805	820	mV
V_F	$I_F=10\text{mA}$	750	825	840	mV
V_F	$I_F=100\text{mA}$	870	920	960	mV
C_T	$V_R=0, f=1.0\text{MHz}$			140	pF

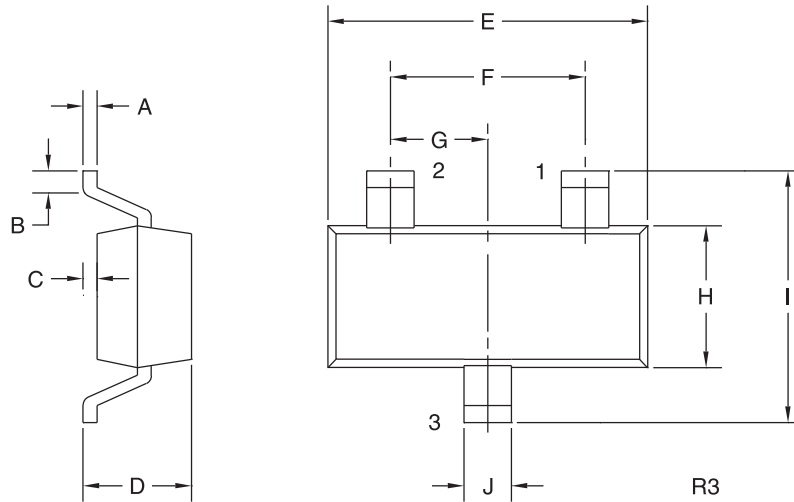
R6 (20-November 2009)

CBAS17

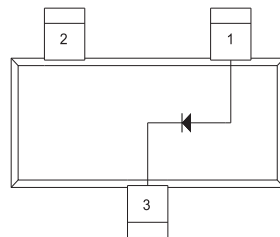
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SOT-23 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



LEAD CODE:

- 1) ANODE
- 2) NO CONNECTION
- 3) CATHODE

MARKING CODE: A91

DIMENSIONS

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

R6 (20-November 2009)